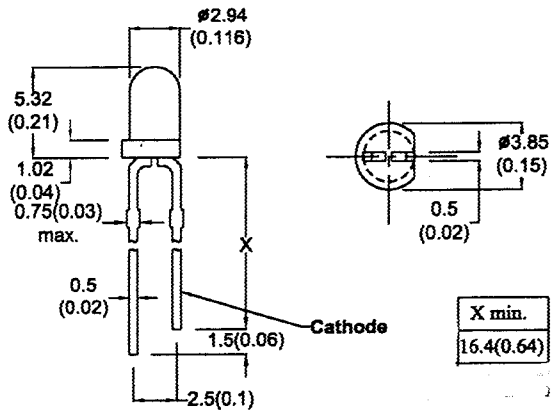
MICRO ELECTRONICS

MI32T

INFRARED EMITTING DIODE

DESCRIPTION

MI32T is GaAlAs infrared emiitting diode molded in 3mm diameter clear transparent lens.



- All dimension in mm(inch)
- No Scale
- Tol. : +/-0.3mm

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	160mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po		0.5		mW	IF=20mA
Forward Voltage	VF			1.6	V	IF=20mA
Reverse Current	IR			100	μA	VR=5V
Half Intensity Beam Angle	θHI		35		degree	IF=20mA
Peak Wavelength	$\lambda\rho$		940		nm	IF=20mA
Spectrum Line Half Width	$\Delta\lambda$		45		nm	IF=20mA

MICRO ELECTRONICS LTD.
38, Hung To Road, Microtron Bulding, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

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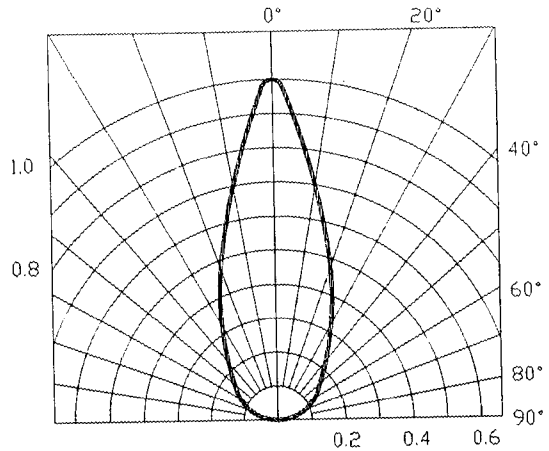
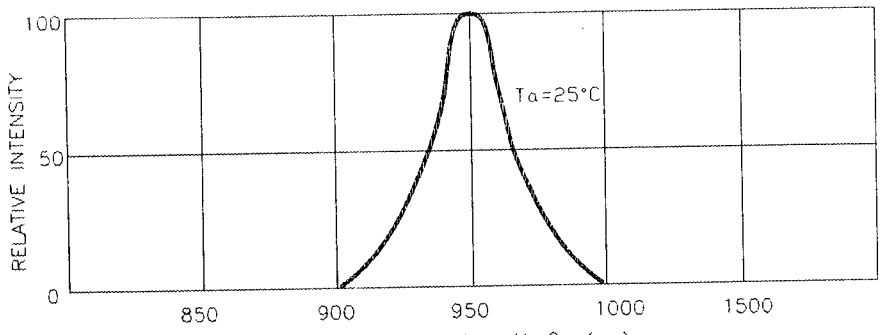
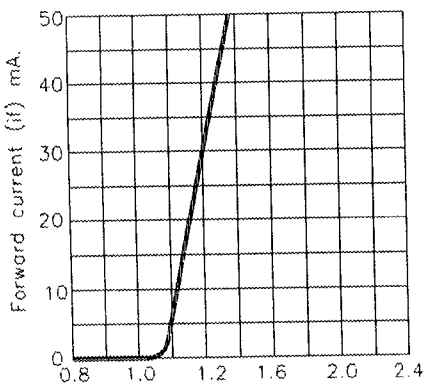


SPATIAL DISTRIBUTION



RELATIVE INTENSITY VS.WAVELENGTH



FORWARD CURRENTS VS..
FORWARD VOLTAGE